INCHANGE Semiconductor

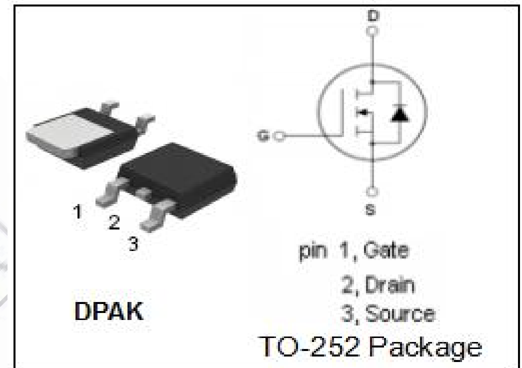
isc N-Channel MOSFET Transistor IPD60R3K4CE,IIPD60R3K4CE

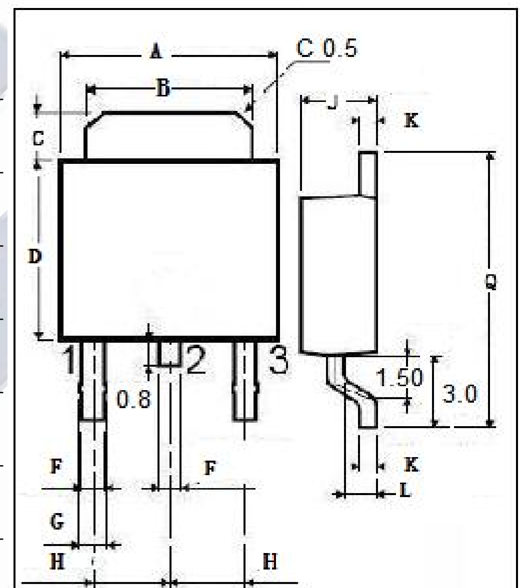
• FEATURES

- Static drain-source on-resistance:
  $R_{DS}(on) \leqslant 3.4\Omega$
- Enhancement mode:
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

• DESCRITION

- Fast switching





DIM	mm MIN	mm MAX
A	6. 40	6. 60
B	5. 20	5. 40
C	1. 15	1. 35
D	5. 70	6. 10
F	0. 65	
G	0. 75	
H	2. 10	2. 50
J	2. 10	2. 40
K	0. 40	0. 60
L	0. 90	1. 10
Q	9. 90	10. 1

• ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{DSS}	Drain-Source Voltage	600	V
V_{GS}	Gate-Source Voltage	±20	V
I_D	Drain Current-Continuous	2.6	A
I_{DM}	Drain Current-Single Pulsed	3.9	A
P_D	Total Dissipation @T_C=25℃	29	W
T_j	Max. Operating Junction Temperature	150	℃
T_{stg}	Storage Temperature	-40~150	℃

• THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
Rth(j-c)	Channel-to-case thermal resistance	4.26	℃/W
Rth(j-a)	Channel-to-ambient thermal resistance	62	℃/W

Download from alldatasheet.com

isc N-Channel MOSFET Transistor IPD60R3K4CE,IIPD60R3K4CE

ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V; I_D=0.25mA	600			V
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS}; I_D=0.04mA	2.5		3.5	V
$R_{DS(on)}$	Drain-Source On-Resistance	V_{GS}=10V; I_D=0.5A			3.4	Ω
I_{GSS}	Gate-Source Leakage Current	V_{GS}=20V; V_{DS}=0V			0.1	μA
I_{DSS}	Drain-Source Leakage Current	V_{DS}=600V; V_{GS}= 0V			1	μA
V_{SD}	Diode forward voltage	I_F=0.6A, V_{GS} = 0V		0.9		V

Download from alldatasheet.com